## **TECHNICAL SPEC FOR Stepper**

System Model: Canon FPA 3000 i5 SN 7122157

Tool has been shut down by Litho tech. Electricity, cooling water, Vacuum and CCA are closed. Cables between Main unit and power box are still connected, locking kit and demounting for transport to be provided by buyer.

Wafer size: 6 inch

Wafer type: Jeida flat

Chuck type: 6 inch pin chuck

Reticle changer type: (Canon standard?)

Inline right or left: left

Particle checker (PPC): Yes

Touch panel type: Canon standard

**Options:** 

Reticle size: 6 inch

**Reticle alignment: see specs below** 

Wafer alignment: see specs below

Auto focus:see specs below

Auto feeder: Yes

Wafer tilt:

Wafer feeder: Yes

Track interface: Yes, tool was used inline, interface is track part

Laser: Hene

Lens data: see below

Stage and U-lens Intensity: 650 mW/cm2 Uniformity: 3.5%

Stage vibration data:

Used for 0.35micron line and space? Y

Chuck maintenance tool: No

Reticle bar code reader: Yes

Cassette bar code reader: No

SW Version:

OS:

Vintage: 2011

Missing/defective parts: none

M I	MODEL	FPA-3000 i5	INSTALLATIO	
Ventex	SN	7122157	INSTALLATIO	I CHECK LIST
CORPORATION	CUSTOMER	ON Semi	STEPPER NAME	STEPPER 16

	DESCRIPTION		Results	UNIT	SPECIFICATION	
LENS DISTORTION	LENS DISTORTION (NA63065)	DX	0.034	μm	< + 0.04	
		DY	0.029		≤ ± 0.04	ок
	LENS DISTORTION Special Mode 1	DX	0.041	μm	NA	NA
		DY	0.057			
DIS	LENS DISTORTION	DX	0.043	μm	NA	NA
TENS	Special Mode 2	DY	0.064			
_	LENS DISTORTION	DX	0.024	μm	NA	NA
	Special Mode 4	DY	0.032		10	ne.
		Initial	0.00			
	SP1	Heated	-0.05	[	Bases < 0.20m	ок
	NA0.5200.60	Cooled	0.05	μm	Range < 0.3µm	OK
EXPOSURE FOCUS STABILITY		Range	0.10			
STAB	SP2 NA0.5500.50	Initial	0.00		Range < 0.3mm	ок
ŝ		Heated	0.10	μm		
ğ		Cooled	0.15			
SUR		Range	0.15			
SP0	SP4 NA0.63σ0.70	Initial	0.05	- μm	Range < 0.3µm	ок
		Heated	0.05			
		Cooled	0.00			
		Range	0.05			
	SP1 NA0.5200.60	Initial	3.22	ppm	Range < 2.0 ppm	ок
<u> </u>		Heated	2.61			
		Cooled	3.52			
STAB		Range	0.92			
NOI	SP2 NA0.5500.50	Initial	3.32	ppm	Range < 2.0 ppm	ок
EXPOSURE MAGNIFICATION STABILITY		Heated	3.25			
		Cooled	3.77			
MAK		Range	0.51			
SURE	SP4	Initial	3.34	ppm	Range < 2.0 ppm	
040		Heated	3.22			ок
	NA0.6300.70	Cooled	2.77			
		Range	0.57			

	Standard/Normal Illumination	Uniformity	1.6	%	≤ 1.0	NG	
		Intensity	8235.0	W/m <sup>2</sup>	≥ 9000		
	Special Illumination Mode 1	Uniformity	1.7	%	NA	NG	
Æ	Special Indianation Probe 1	Intensity	11478	W/m²	NA		
YSTI	Special Illumination Mode 2	Uniformity	2.1	%	NA	NG	
No	Special Indifination Probe 2	Intensity	11908	W/m <sup>2</sup>	NA		
ILLUMINATION SYSTEM	Special Illumination Mode 4	Uniformity	1.3	%	NA		
IMN	Special Illumination Mode 4	Intensity	10890	W/m²	NA	NG	
Ξ	L.I. ACCURACY		0.45	%	≤ 1.0	ОК	
		θ	-113.6	ppm	≤ 3000		
	MASKING BLADE ACCURACY	GZW	20	μm	≤ 60	ок	
		Total	32.5	μm	≤ ± 110	1	
		F(30)	0.038	μm	<b>3σ ≤ 0.08</b>		
	FOCUS - TILT STABILITY	X(3σ)	2.909		3σ≤6	ок	
		Υ(3σ)	2.754	ppm	30 2 6		
	FOCUS - TILT REPEATABILITY	F(30)	0.08	μm	<b>3</b> σ ≤ 0.10		
EM		X(3σ)	2.7		3σ≤7	ок	
FOCUS TILT SYSTEM		Υ(3σ)	3.8	ppm	30 5 7		
E.	GLOBAL - TILT MEASUREMENT REPEATABILITY	X(3σ)	0.6		3σ ≤ 4	ок	
ISUC	GLOBAL - TILL MEASUREMENT REPEATABLETT	Υ(3σ)	0.7	ppm	30 5 4	OK	
ğ	GLOBAL - TILT ACCURACY	X(3σ)	1.8		3σ ≤ 8	ок	
	GLOBAL - TILL ACCONNET	Υ(3σ)	1.0	ppm	30 2 0	UK I	
	TILT SENSOR UNEVEN FOCUS (DxD ON)	v	0.0	ppm	≤ ± 4	ОК	
	UNEVEN FOCUS (TSOC) (DxD OFF)	v	1.5	ppm	≤ ± 6	ОК	
	ALFC MEASUREMENT REPEATABILITY	TABILITY 3σ 0.03 μm 3c	<b>3</b> σ ≤ 0.10	ОК			
TVPA		X	1.94		< 3.0	ок	
Ę	TV PRE-ALIGNMENT ACCURACY (DARK FIELD)	Y	2.55	μm	≤ 3.0		

		Ortho	-0.05			
	XYSA	Scal X	0.05	ppm	≤ ± .5	ок
		Scal Y	-0.03			
		XX (3σ)	0.011			
		XY (3σ)	0.011	ł		
	STEPPING ACCURACY WAFER 1		0.011	μm	3σ ≤ 0.040	ок
		YX (3σ)		ł		
щ		YY(3σ)	0.014			
STAG		XX (3σ)	0.010	ł		
WAFER STAGE	STEPPING ACCURACY WAFER 2	XY (3σ)	0.009	μm	3σ ≤ 0.040	ок
WA		YX (3σ)	0.015	ļ		
		YY(3σ)	0.015			
		XX (3σ)	0.011	ļ		
	STEPPING ACCURACY WAFER 3	XY (3σ)	0.009	μm	3σ ≤ 0.040	ок
		YX (3σ)	0.014			
		YY(3σ)	0.011			
	STEPPING REPEATABILITY	Χ(3σ)	0.023	μm	3σ ≤ 0.035	ок
		Υ(3σ)	0.013	<b>-</b>		
SRC	SRC MEASUREMENT REPEATABILITY	3σ	0.30	ppm	3σ ≤ 0.5	ОК
E	ROC MEASUREMENT REPEATABILITY	XL(3σ)	0.004	μm	3σ ≤ 0.01	ок
MEN		YL(3σ)	0.002			
LIGN 1		XR(3σ)	0.005			
JEA		YR(3σ)	0.002			
REFICLE ALIGNMENT	RETICLE ROTATION ACCUARACY		-0.003	μm	≤ <b>±</b> 0.01	ОК
R	RETICLE ROTATION REPEATABILITY		0.001	μm	≤ ± 0.02	ОК
	BLC STABILITY (MODE 1)	Χ(3σ)	0.005	μm	3σ ≤ 0.030	ок
		Υ(3σ)	0.008			
		RNG(X)	0.007	μm	D	ок
		RNG (Y)	0.012		Range ≤ 0.03	
	BLC STABILITY (MODE 2)	X(3σ)	0.005	μm	3σ ≤ 0.030	ок
INE		Υ(3σ)	0.004			
BASELINE		RNG(X)	0.006	μm	Range ≤ 0.03	
•		RNG (Y)	0.006			ок
		Χ(3σ)	0.007			ок
		Υ(3σ)	0.006	μm	3σ ≤ 0.031	
	BLC STABILITY (MODE 4)	RNG(X)	0.009			ок
		RNG (Y)	0.008	μm	Range ≤ 0.03	

SNMEN.		x	0.023			
	AGA ACCURACY MODE 1 ( m  + 30)	Y	0.026	μm	mean  + 3σ < 0.05	OK
	AGA ACCURACY MODE 2 ( m  + 30)	x	0.035	μm	mean  + 3σ < 0.05	ок
DALI		Y	0.027			
AUT	AGA ACCURACY MODE 4 ( m  + 3σ)	x	0.024	μm	mean  + 3σ < 0.05	ок
		Y	0.031			
		XL	5.796			
			6.016	μm	3σ ≤ 40	ок
			8.58			
		YR	7.315			
TPD	THROUGHPUT 6" WAFER TYPE-L WF	DxD ON	128.5	WPH	>120	ок
	THROUGHPOT O WAFER TIPE E WE	DxD OFF	130.1		>120	ок
	WAFER CHUCK FLATNESS	🗆 22mm	0.44	μm		